MBR1635, MBR1645, MBRB1645

MBR1645 is a Preferred Device

SWITCHMODE™ Power Rectifiers 16 A, 35 and 45 V

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These state-of-the-art devices use the Schottky Barrier principle with a platinum barrier metal.

Features

- Guard-ring for Stress Protection
- Low Forward Voltage
- 175°C Operating Junction Temperature
- Pb-Free Packages are Available

Mechanical Characteristics:

- Case: Epoxy, Molded
- Weight: 1.9 Grams for TO-220
 - 1.7 Grams for D²PAK
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperature for Soldering Purposes: 260°C Max. for 10 Seconds

MAXIMUM RATINGS

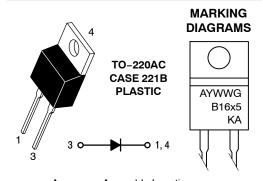
Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage MBR1635 MBR1645 MBRB1645	V _{RRM} V _{RWM} V _R	35 45 45	V
Average Rectified Forward Current Delay (Rated V _R , T _C = 163°C) Total Device	I _{F(AV)}	16	Α
Peak Repetitive Forward Current, Per Leg (Rated V _R , Square Wave, 20 kHz, T _C = 157°C) Total Device	I _{FRM}	32	А
Non-Repetitive Peak Surge Current (Surge Applied at Rated Load Conditions Halfwave, Single Phase, 60 Hz)	I _{FSM}	150	Α
Peak Repetitive Reverse Surge Current (2.0 μs, 1.0 kHz)	I _{RRM}	1.0	Α
Storage Temperature Range	T _{stg}	-65 to +175	°C
Operating Junction Temperature (Note 1)	T_J	-65 to +175	°C
Voltage Rate of Change (Rated V _R)	dv/dt	10,000	V/μs

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

 The heat generated must be less than the thermal conductivity from Junction-to-Ambient: dP_D/dT_J < 1/R_{θ,JA}.

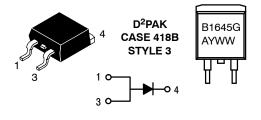


ON Semiconductor®



A = Assembly Location
Y = Year
WW = Work Week
B16x5 = Device Code
x = 3 or 4

KA = Diode Polarity
G = Pb-Free Package



B1645 = Device Code A = Assembly Location

Y = Year WW = Work Week G = Pb-Free Package

ORDERING INFORMATION

Device	Package	Shipping		
MBR1635	TO-220	50 Units / Rail		
MBR1635G	TO-220 (Pb-Free)	50 Units / Rail		
MBR1645	TO-220	50 Units / Rail		
MBR1645G	TO-220 (Pb-Free)	50 Units / Rail		
MBRB1645T4G	D ² PAK (Pb-Free)	800 Units / Rail		

Preferred devices are recommended choices for future use and best overall value.

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THERMAL CHARACTERISTICS

Characteristic		Symbol	Value	Unit
Maximum Thermal Resistance, Junction		$R_{ heta JC}$	1.5	°C/W

ELECTRICAL CHARACTERISTICS

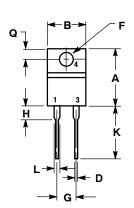
Characteristic	Symbol	Value	Unit
Maximum Instantaneous Forward Voltage (Note 2) ($i_F = 16 \text{ Amps}, T_C = 125^{\circ}\text{C}$) ($i_F = 16 \text{ Amps}, T_C = 25^{\circ}\text{C}$)	VF	0.57 0.63	٧
Maximum Instantaneous Reverse Current (Note 2) (Rated dc Voltage, $T_C = 125^{\circ}C$) (Rated dc Voltage, $T_C = 25^{\circ}C$)	İR	40 0.2	mA

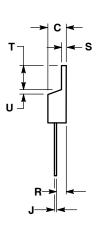
^{2.} Pulse Test: Pulse Width = 300 μs, Duty Cycle ≤ 2.0%.

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PACKAGE DIMENSIONS

TO-220 PLASTIC CASE 221B-04 ISSUE E





- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
Α	0.595	0.620	15.11	15.75
В	0.380	0.405	9.65	10.29
С	0.160	0.190	4.06	4.82
D	0.025	0.035	0.64	0.89
F	0.142	0.161	3.61	4.09
G	0.190	0.210	4.83	5.33
Н	0.110	0.130	2.79	3.30
J	0.014	0.025	0.36	0.64
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.14	1.52
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.14	1.39
T	0.235	0.255	5.97	6.48
U	0.000	0.050	0.000	1.27